

N- and P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
	V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
N-Channel	20	0.0145 at $V_{GS} = 10$ V	9.6
		0.017 at $V_{GS} = 4.5$ V	8.6
P-Channel	- 20	0.033 at $V_{GS} = - 4.5$ V	- 6.2
		0.050 at $V_{GS} = - 2.5$ V	- 5

FEATURES

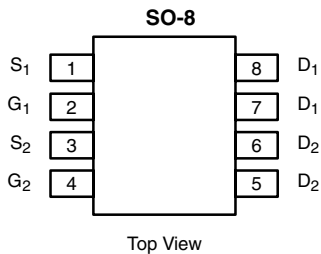
- TrenchFET[®] Power MOSFET

APPLICATIONS

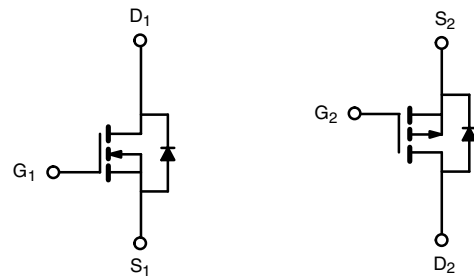
- Level Shift
- Load Switch



RoHS*
COMPLIANT



Ordering Information: Si4511DY-T1
Si4511DY-T1-E3 (Lead (Pb)-Free)



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		10 secs	Steady	10 secs	Steady		
Drain-Source Voltage	V_{DS}	20		- 20		V	
Gate-Source Voltage	V_{GS}	± 16		± 12			
Continuous Drain Current ($T_J = 150$ °C) ^{a, b}	I_D	$T_A = 25$ °C	9.6	7.2	- 6.2	- 4.6	A
		$T_A = 70$ °C	7.7	5.8	- 4.9	- 3.7	
Pulsed Drain Current	I_{DM}	40		- 40			
Continuous Source Current (Diode Conduction) ^a	I_S	1.7	0.9	- 1.7	0.9		
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	2	1.1	2	1.1	W
		$T_A = 70$ °C	1.3	0.7	1.3	0.7	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150				°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		Typ	Max	Typ	Max		
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	50	62.5	50	62.5	°C/W
		Steady State	85	110	90	110	
Maximum Junction-to-Foot (Drain)	R_{thJF}	30	40	30	35		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
b. $t \leq 10$ sec

* Pb containing terminations are not RoHS compliant, exemptions may apply.

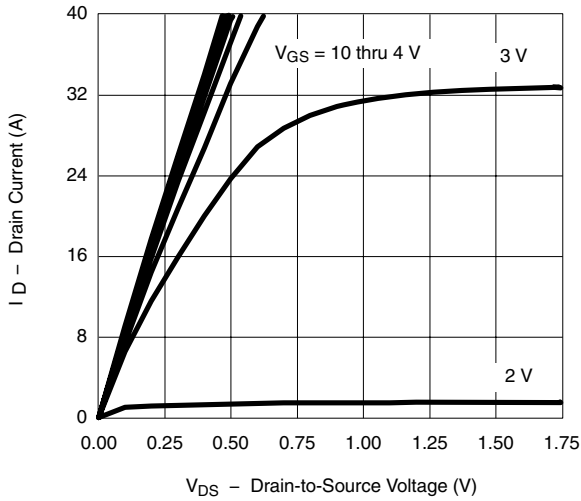
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	0.6		1.8	V
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-0.6		1.4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$	N-Ch			± 100	nA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$	P-Ch			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	μA
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			-1	
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	N-Ch			5	
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	P-Ch			-5	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	N-Ch	40			A
		$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	P-Ch	-40			
Drain-Source On-State Resistance ^b	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 9.6\text{ A}$	N-Ch		0.0115	0.0145	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -6.2\text{ A}$	P-Ch		0.022	0.033	
		$V_{GS} = 4.5\text{ V}, I_D = 8.6\text{ A}$	N-Ch		0.0135	0.017	
		$V_{GS} = -2.5\text{ V}, I_D = -5\text{ A}$	P-Ch		0.035	0.050	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 9.6\text{ A}$	N-Ch		33		S
		$V_{DS} = -15\text{ V}, I_D = -6.2\text{ A}$	P-Ch		17		
Diode Forward Voltage ^b	V_{SD}	$I_S = 1.7\text{ A}, V_{GS} = 0\text{ V}$	N-Ch		0.8	1.2	V
		$I_S = -1.7\text{ A}, V_{GS} = 0\text{ V}$	P-Ch		-0.8	-1.2	
Dynamic^a							
Total Gate Charge	Q_g	N-Channel $V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 9.6\text{ A}$ P-Channel $V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -6.2\text{ A}$	N-Ch		11.5	18	nC
Gate-Source Charge	Q_{gs}		N-Ch		3.7		
Gate-Drain Charge	Q_{gd}		P-Ch		4.1		
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_G = 6\text{ }\Omega$ P-Channel $V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$	N-Ch		12	20	ns
Rise Time	t_r		P-Ch		25	40	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		12	20	
Fall Time	t_f		P-Ch		30	45	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	N-Ch		50	100	
		$I_F = -1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	P-Ch		40	80	

Notes

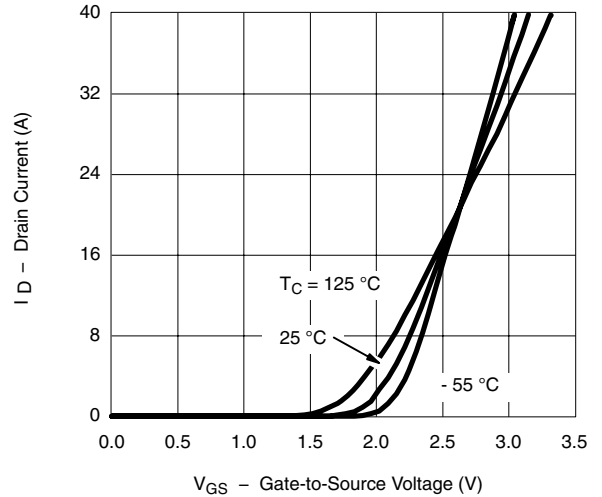
- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

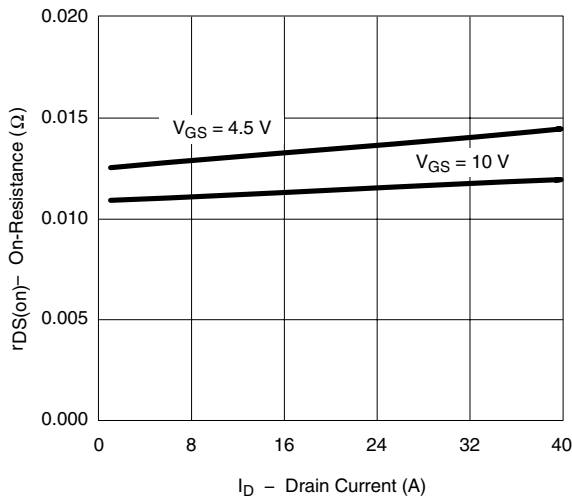
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



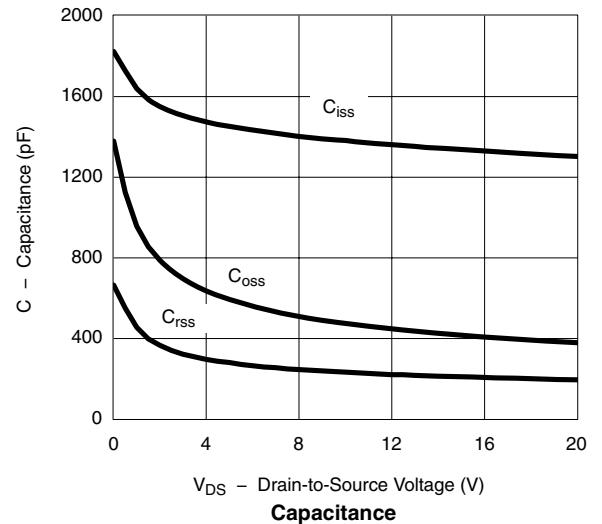
Output Characteristics



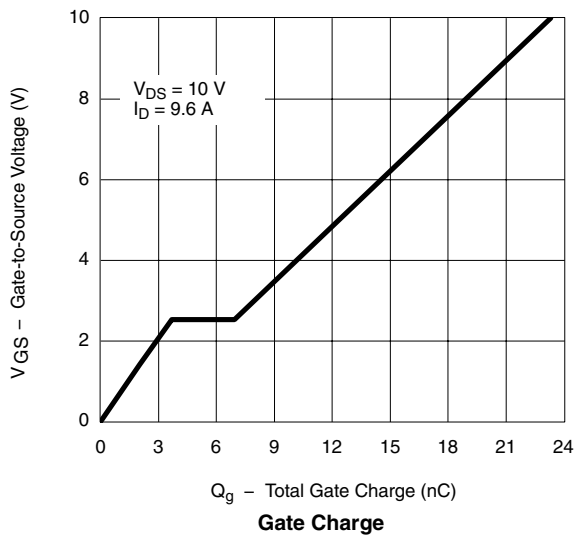
Transfer Characteristics



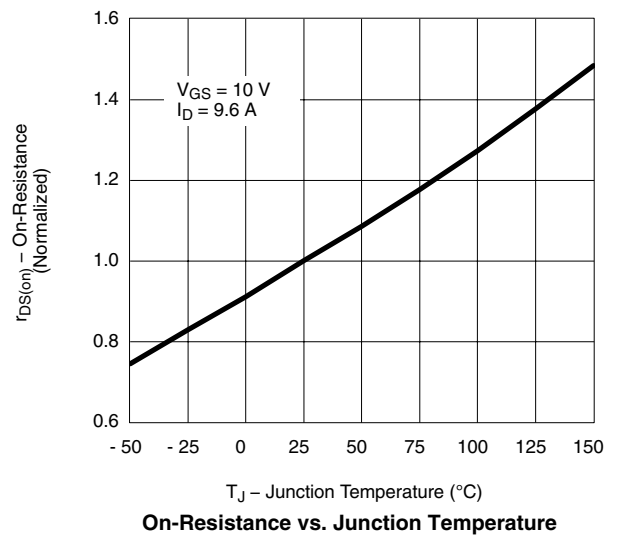
On-Resistance vs. Drain Current



Capacitance

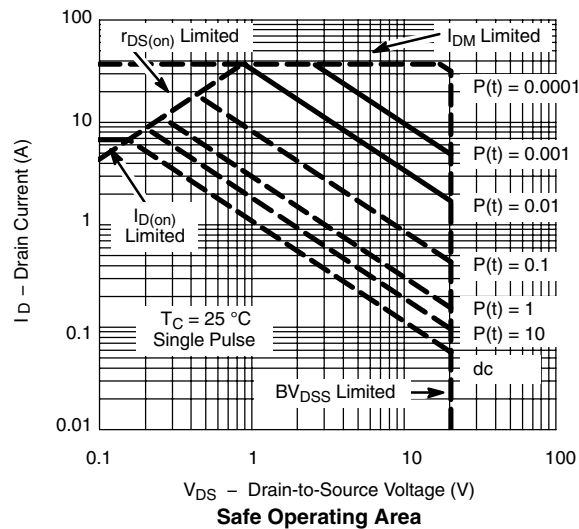
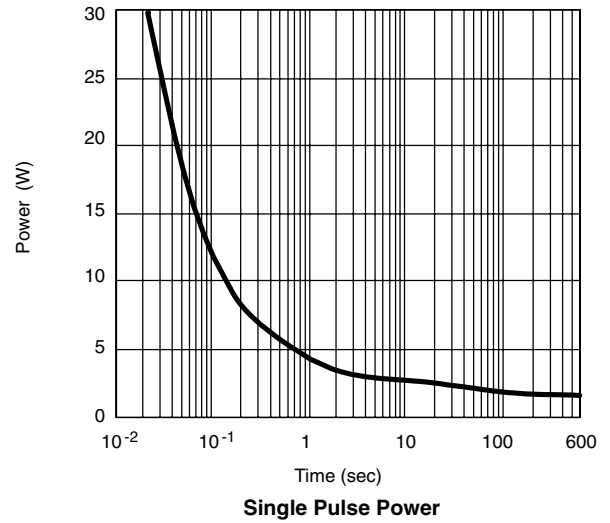
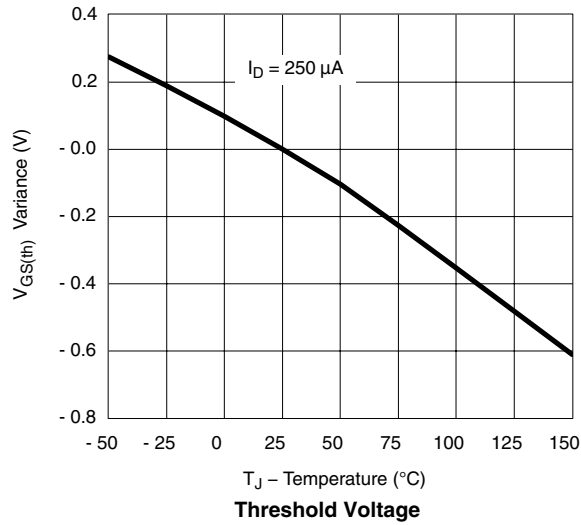
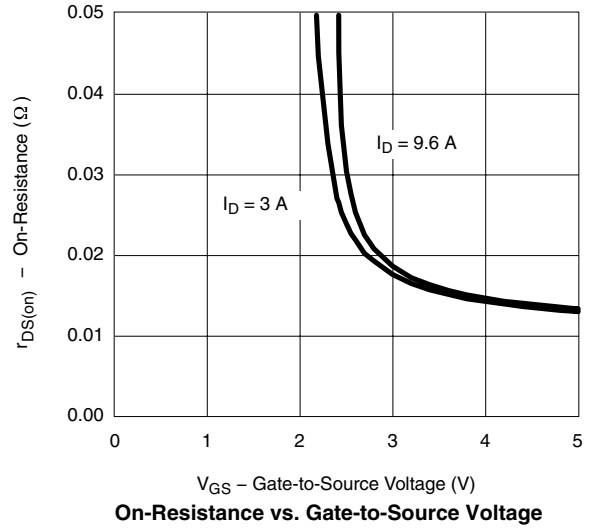
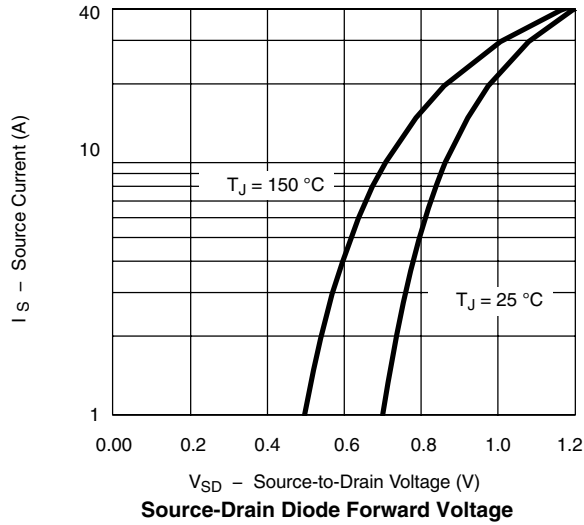


Gate Charge



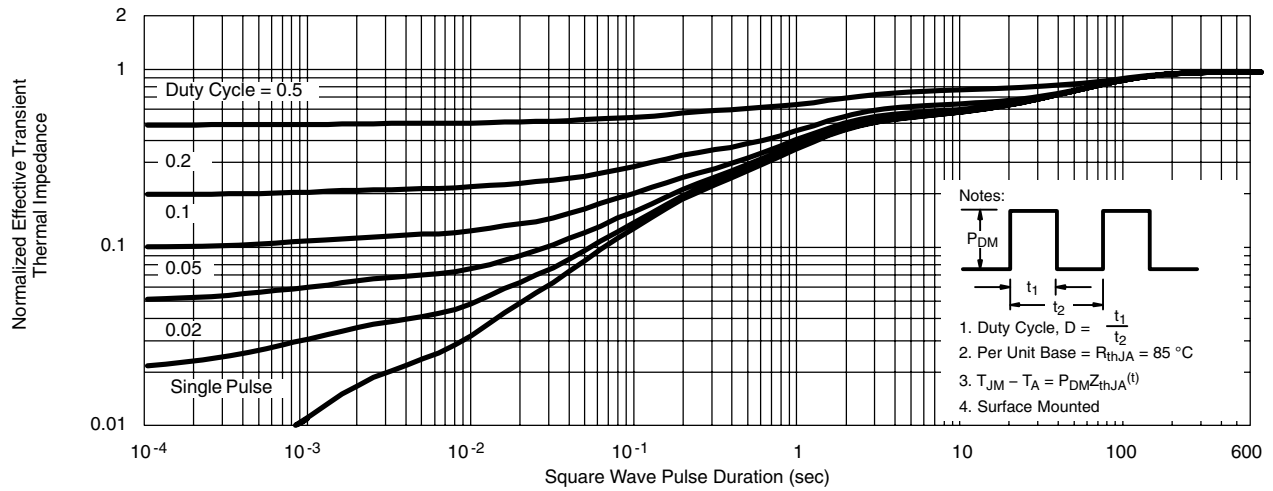
On-Resistance vs. Junction Temperature

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted

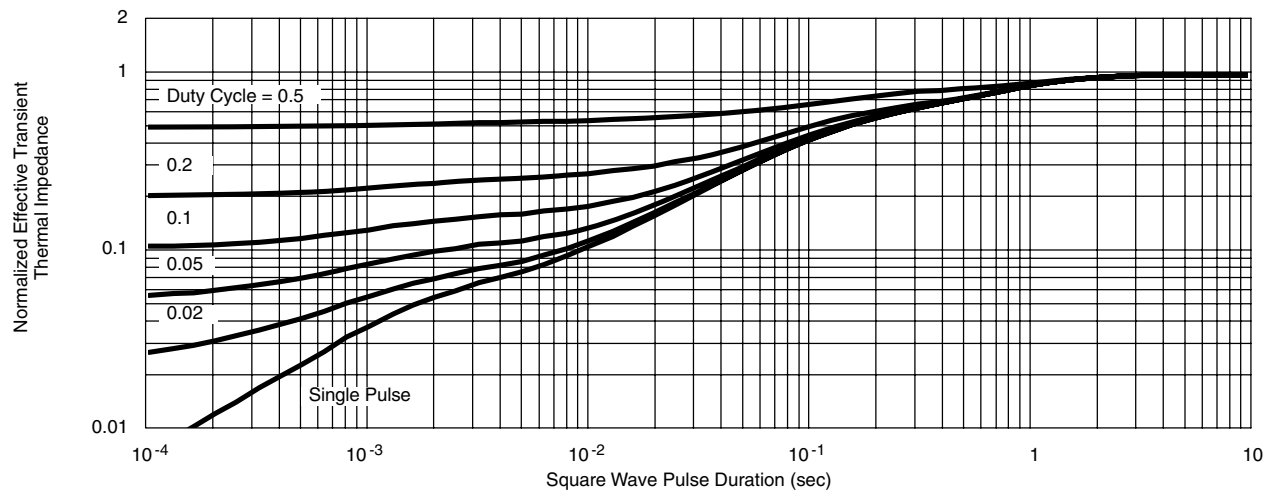




N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted

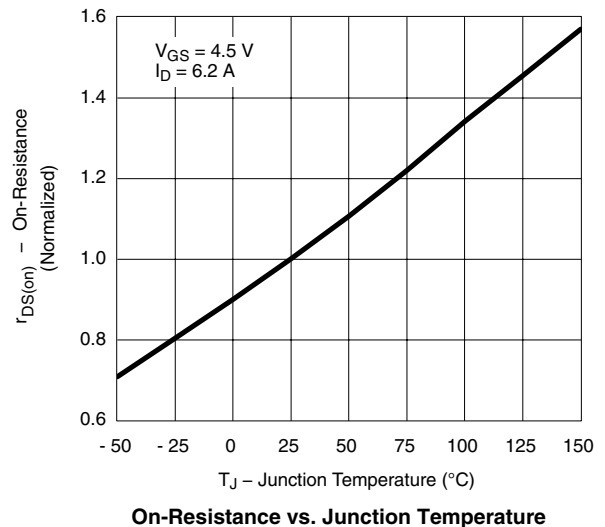
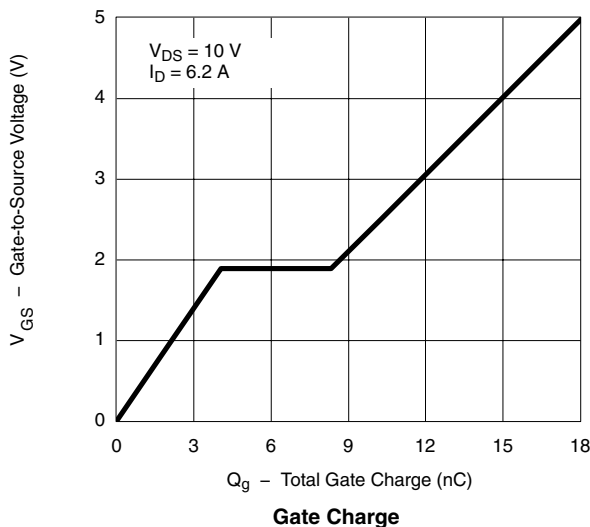
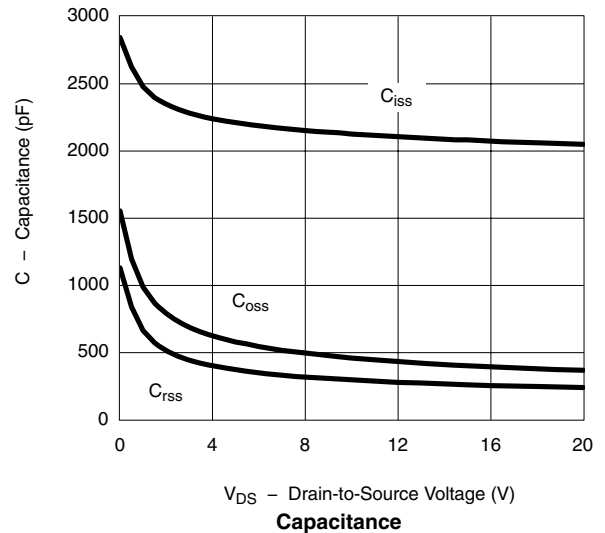
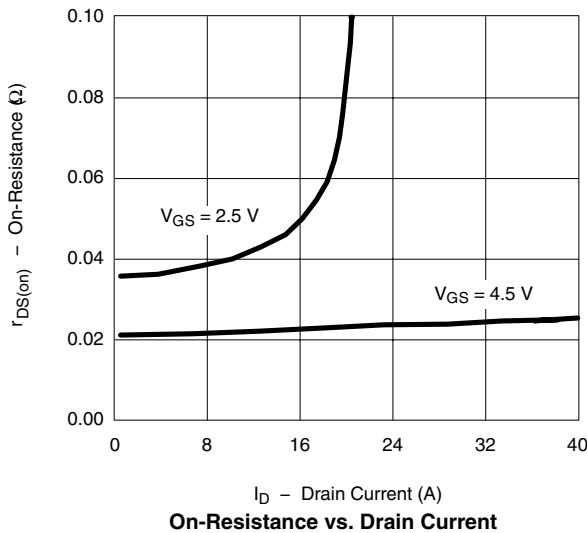
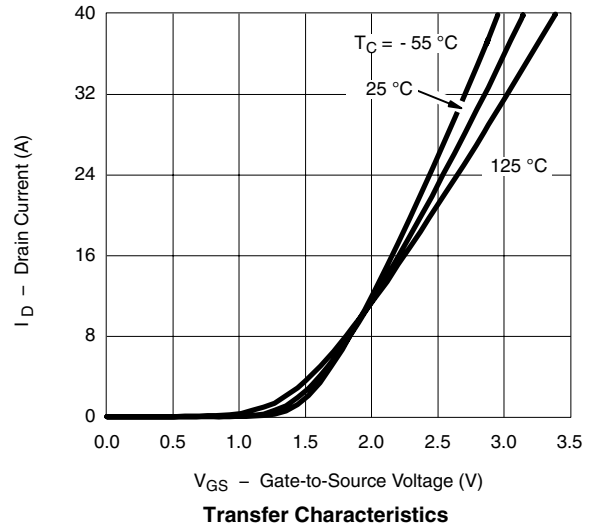
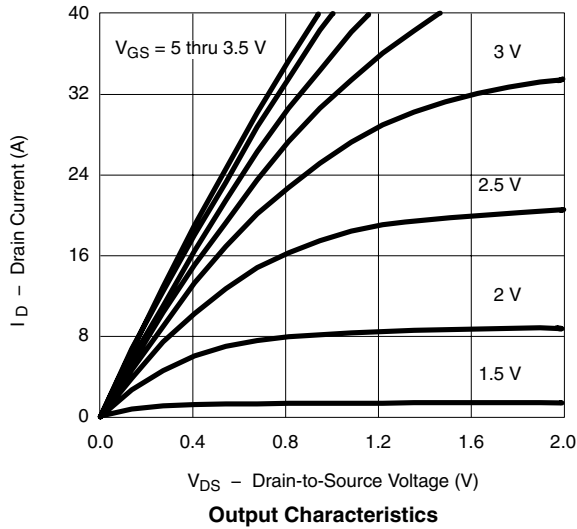


Normalized Thermal Transient Impedance, Junction-to-Ambient



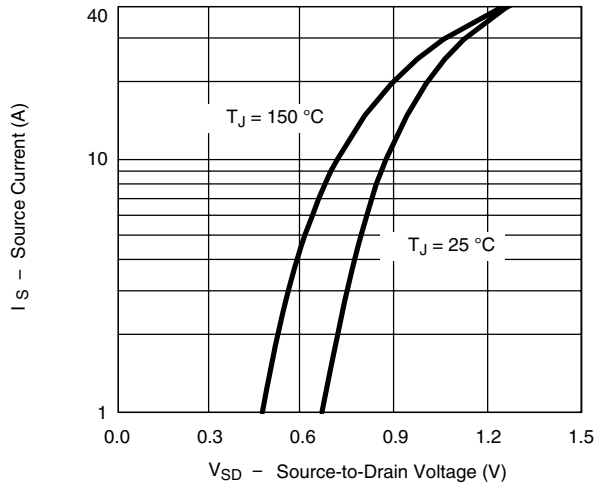
Normalized Thermal Transient Impedance, Junction-to-Foot

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted

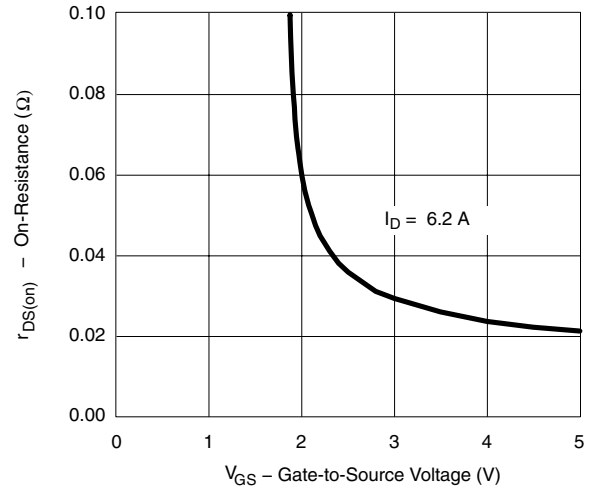




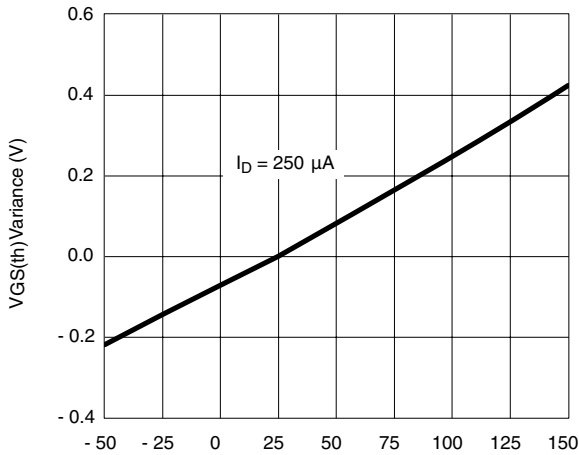
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



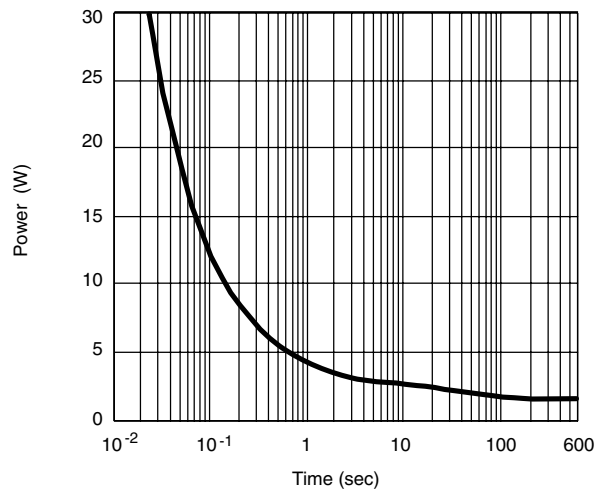
Source-Drain Diode Forward Voltage



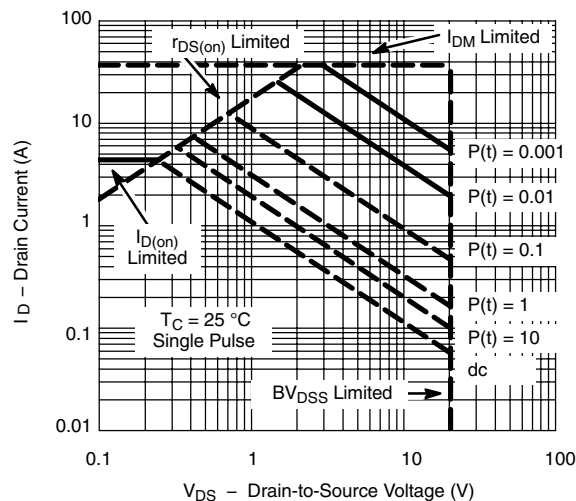
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

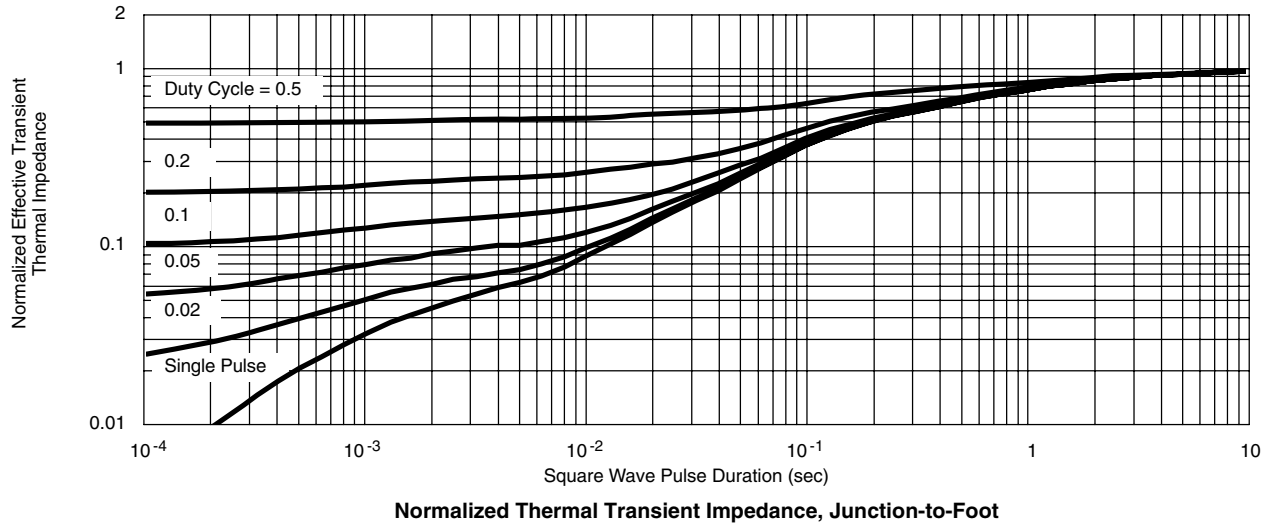
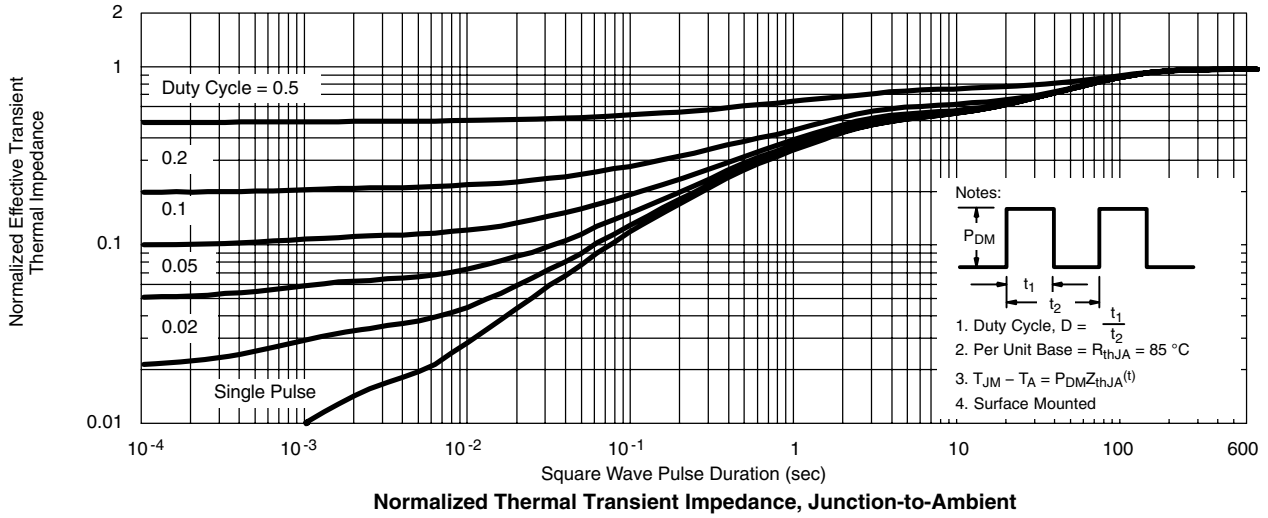


Single Pulse Power



Safe Operating Area

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?72223>.



Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.